

IN THE SPECIFICATION:

Please replace paragraph number [0001] with the following rewritten paragraph:

[0001] This application is a continuation of application Serial No. 10/121,645, filed April 12, 2002, ~~pending~~ now U.S. Patent 6,670,284, issued December 30, 2003, which is a continuation of application Serial No. 09/095,477, filed June 10, 1998, now U.S. Patent 6,461,970, issued October 8, 2002.

Please replace paragraph number [0007] with the following rewritten paragraph:

[0007] An exemplary ARC is a polymer film that may be disposed on the substrate layer by spin-on techniques. Other anti-reflective materials, such as the silicon-rich silicon nitride DARC disclosed in United States ~~Patents~~ Patent 5,378,659, which issued to Roman et al. on January 3, 1995; and 5,539,249, which issued to Roman et al. on July 23, 1996; and the silicon, oxygen and nitrogen DARC materials disclosed in United States Patent 5,698,352, which issued to Ogawa et al. on December 16, 1997, may be deposited by known processes, such as chemical vapor deposition (CVD) or plasma-enhanced CVD (PECVD).